

LOW VOLTAGE NON-VOLATILE MEMORY CELL

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This application is a division of application serial NO. 10/283,736 filed 10/29/2002, now patent NO. 6,671,205, which is a division of application serial NO. 09/742,275 filed on 12/29/2000, now patent NO. 6,496,416.

FIELD OF THE INVENTION

[0001] The present invention relates to a structure for measuring mask and layer alignment in semiconductor fabrication processes.

RELATED ART

[0002] A non-volatile memory cell is a memory cell that retains its stored information even if power is removed from the cell. In a conventional nonvolatile memory cell, a floating gate structure is commonly incorporated to provide this information storage function. Fig. 1 shows an example of a conventional floating gate memory cell 100. Memory cell 100 comprises a polysilicon floating gate 121 surrounded by an insulation material (e.g. silicon dioxide) 150. Floating gate 121 is located over a portion (channel) of a p-type body region 113 extending between an n-type source region 111 and an n-type drain region 112, all of which are formed in a substrate (e.g. silicon wafer) 101. A control gate 120 is located on the portion of insulation material 150 over floating gate 121. Source region 111, drain region 112, and control gate 120 are coupled to receive a source voltage V_s , a drain voltage V_d , and a gate voltage V_g , respectively.

[0003] Current between source region 111 and drain region 112 is controlled by the programmed/erased state of floating gate 121. This programmed/erased state is determined by the number of electrons stored (captured) in floating gate 121. In an unprogrammed state, a gate voltage V_g applied to control gate 120 controls the current flow between source region 111 and drain region 112 (i.e. memory cell 100 conducts when voltage V_g is HIGH, and does not conduct when voltage V_g is LOW). To program memory cell 100, electrons are injected into floating gate 121 until it stores a net negative charge that is sufficient to shift the threshold voltage of memory cell 100. Once programmed, memory cell 100